

**Silicon PNP transistor epitaxial type
B5947**

[Applications]

DC-DC converter, Strobe flash, Relay drive, Inverter drive
with small $V_{CE(sat)}$ and high current

[Feature]

High collector current

Low collector-emitter saturation voltage $V_{CE(sat)} = -350\text{mV(Max.)}$ at $I_C = -4\text{A}$

[Absolute maximum ratings ($T_a=25\text{C}$)]

| Characteristic | Symbol | Maximum ratings | Unit |
|---------------------------|-----------|-----------------|------|
| Collector-base voltage | VCBO | -30 | V |
| Collector-emitter voltage | VCEO | -20 | V |
| Emitter-base voltage | VEBO | -6 | V |
| Collector current | I_C | -5 | A |
| Junction temperature | T_j | 150 | C |
| Storage temperature | T_{stg} | -55 to 150 | C |

[Electrical characteristics ($T_a=25\text{C}$)]

| Characteristic | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------------------|---------------|------|-------|------|---------------|--|
| Collector-base breakdown voltage | BVCBO | -30 | - | - | V | $I_C = -50\mu\text{A}$, $I_E = 0\text{A}$ |
| Collector-emitter breakdown voltage | BVCEO | -20 | - | - | V | $I_C = -1\text{mA}$, $I_B = 0\text{A}$ |
| Emitter-base breakdown voltage | BVEBO | -6 | - | - | V | $I_E = -50\mu\text{A}$, $I_C = 0\text{A}$ |
| Collector cut-off current | ICBO | - | - | -0.5 | μA | $V_{CB} = -20\text{V}$, $I_E = 0\text{A}$ |
| Emitter cut-off current | IEBO | - | - | -0.5 | μA | $V_{EB} = -5\text{V}$, $I_E = 0\text{A}$ |
| DC current gain | h_{FE} | 82 | - | 390 | - | $V_{CE} = -2\text{V}$, $I_C = -500\text{mA}$ |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | - | -0.35 | -1 | V | $I_C = -4\text{A}$, $I_B = -0.1\text{A}$ |
| Transition frequency | f_T | - | 120 | - | MHz | $V_{CE} = -6\text{V}$, $I_E = 50\text{mA}$ |
| Collector output capacitance | C_{ob} | - | 60 | - | pF | $V_{CB} = -20\text{V}$, $f = 1\text{MHz}$, $I_E = 0\text{A}$ |

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

Fig.1 VBE(on) - IC
at VCE= -2V, Ta= 25C

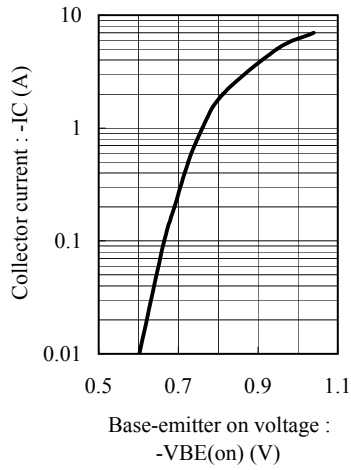


Fig.2 hFE - IC
at VCE= -2V, Ta= 25C

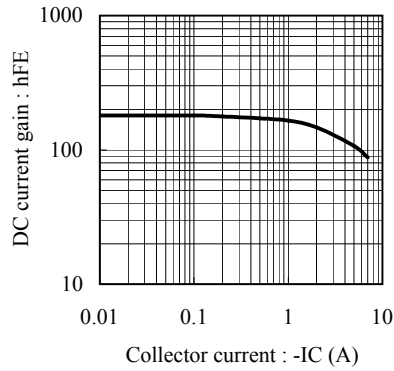


Fig.3 VCE(sat) - IC
at IC/IB= 40, Ta= 25C

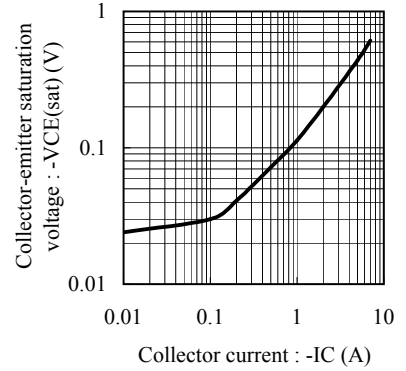


Fig.4 VBE(sat) - IC
at IC/IB= 10, Ta= 25C

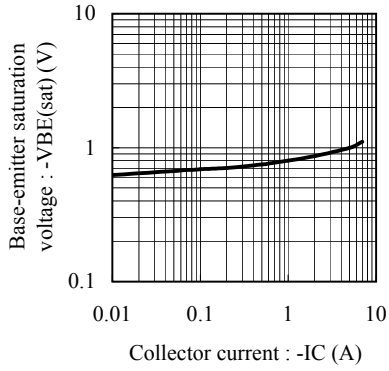


Fig.5 fT - IE
at VCE= -6V, Ta= 25C

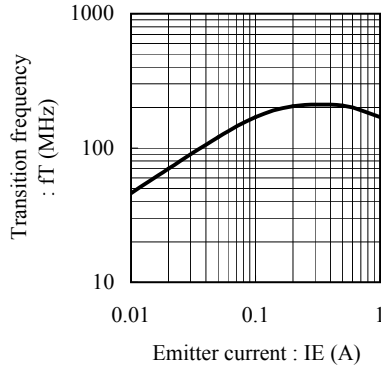


Fig.6 Cob - VCB
at f= 1MHz, Ta= 25C

